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**BOX AF**

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

NOV 14 2002

PATENT & TRADEMARK OFFICE

re the Application of: IRINO, Kiyoshi

Serial No.: 09/428,052

AF/2815  
#20/6  
Am dt  
Group Art Unit: 2815 ~~2815~~

Filed: October 27, 1999

Examiner: Jose R. Diaz  
J. M. Chinella  
11/20/02

P.T.O. Confirmation No.: 4139

For: **METHOD FOR FABRICATING A SEMICONDUCTOR DEVICE CONTAINING NITROGEN IN A GATE OXIDE FILM (As Amended)**

**RESPONSE UNDER 37 CFR §1.116**

**- EXPEDITED RESPONSE -  
GROUP ART UNIT 2815**

**BOX AF**

Commissioner for Patents  
Washington, D.C. 20231

November 14, 2002

Sir:

In response to the Office Action dated August 14, 2002, please amend the above-identified application as follows:

**IN THE CLAIMS:**

Please amend claim 10 as follows:

10. (Six Times Amended) A method of fabricating a semiconductor device, comprising the

steps of:

forming a gate oxide film on a substrate by a thermal oxide film;

forming a gate electrode pattern on said gate oxide film such that said gate electrode pattern

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